

Title (en)

Dummy end-gate based anti-fuse device for finFET technologies

Title (de)

Antisicherungsvorrichtung für finFET-Technologien auf Blind-Endgate-Basis

Title (fr)

Dispositif anti-fusible à base de grille d'extrémité factice pour technologies finFET

Publication

EP 2894668 B1 20170816 (EN)

Application

EP 14004370 A 20141222

Priority

- US 201461927437 P 20140114
- US 201414173744 A 20140205

Abstract (en)

[origin: EP2894668A1] An anti-fuse device for fin field-effect transistor (finFET) technology includes a dummy gate, an electrically conductive contact, and a diffusion contact. The dummy gate is formed over an end-corner of a fin. The electrically conductive contact is disposed on a portion of the dummy gate and can be used as a first electrode of the device. The diffusion contact is disposed over the fin and can be used as a second electrode of the device.

IPC 8 full level

H01L 23/525 (2006.01); **G11C 17/16** (2006.01); **H01L 27/12** (2006.01); **H01L 29/66** (2006.01); **H01L 29/78** (2006.01); **H10B 69/00** (2023.01)

CPC (source: EP US)

H01L 23/5252 (2013.01 - EP US); **H01L 29/66545** (2013.01 - US); **H01L 29/66795** (2013.01 - US); **H01L 29/7851** (2013.01 - US); **H10B 20/20** (2023.02 - US); **H10B 20/25** (2023.02 - EP); **G11C 17/16** (2013.01 - EP US); **H01L 29/785** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US)

C-Set (source: EP US)

H01L 2924/0002 + **H01L 2924/00**

Designated contracting state (EPC)

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DOCDB simple family (publication)

EP 2894668 A1 20150715; **EP 2894668 B1 20170816**; CN 104779237 A 20150715; CN 104779237 B 20190212; CN 204696122 U 20151007; HK 1209900 A1 20160408; US 2015200196 A1 20150716; US 9165936 B2 20151020

DOCDB simple family (application)

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